

Title (en)  
METHOD FOR PRODUCING A MICROELECTRONIC COMPONENT AND COMPONENT PRODUCED ACCORDING TO SAID METHOD

Title (de)  
VERFAHREN ZUR HERSTELLUNG EINES MIKROELEKTRONISCHEN BAUELEMENTS UND DANACH HERGESTELLTES BAUELEMENT

Title (fr)  
PROCEDE DE PRODUCTION D'UN COMPOSANT MICROELECTRONIQUE ET COMPOSANT PRODUIT SELON CE PROCEDE

Publication  
**EP 1346403 A2 20030924 (DE)**

Application  
**EP 01988040 A 20011218**

Priority  
• DE 10064479 A 20001222  
• EP 0114955 W 20011218

Abstract (en)  
[origin: WO02052626A2] The invention relates to methods for producing a semiconductor element in a GaAs compound semiconductor material, especially a heterostructure GaAs semiconductor material, for example a hetero-bipolar transistor. The invention allows production of a low-impedance contact resistance with high long-term stability of the component properties in a simple and cost-effective process profile.

IPC 1-7  
**H01L 21/285**; **H01L 29/45**

IPC 8 full level  
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Citation (search report)  
See references of WO 02052626A2

Citation (examination)  
US 5411632 A 19950502 - DELAGE SYLVAIN [FR], et al

Designated contracting state (EPC)  
AT BE CH CY DE DK ES FI FR GB GR IE IT LI LU MC NL PT SE TR

DOCDB simple family (publication)  
**WO 02052626 A2 20020704**; **WO 02052626 A3 20030213**; CN 1222984 C 20051012; CN 1481579 A 20040310; DE 10064479 A1 20020704; EP 1346403 A2 20030924; TW 550715 B 20030901

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**EP 0114955 W 20011218**; CN 01820891 A 20011218; DE 10064479 A 20001222; EP 01988040 A 20011218; TW 90131716 A 20011220